

Electronic Supplementary Information

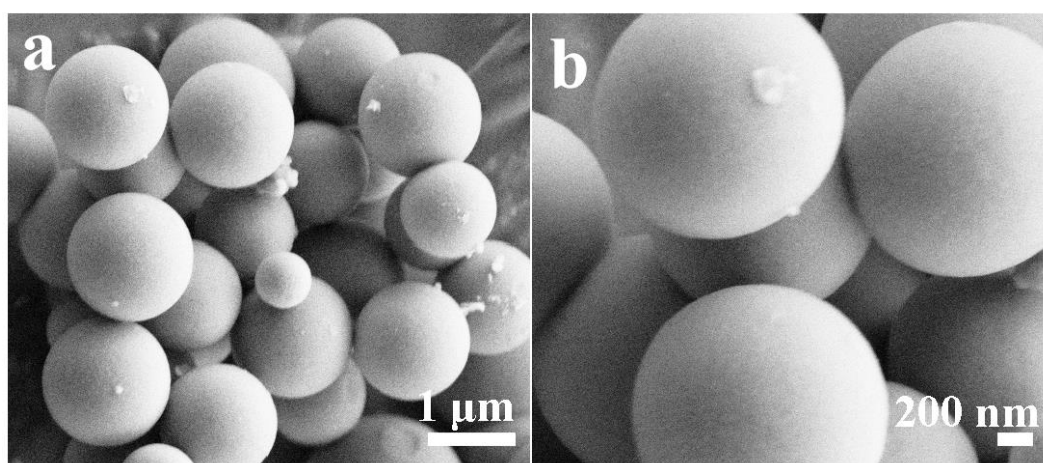


Fig. S1 (a, b) SEM images of NiZn-MOFs.

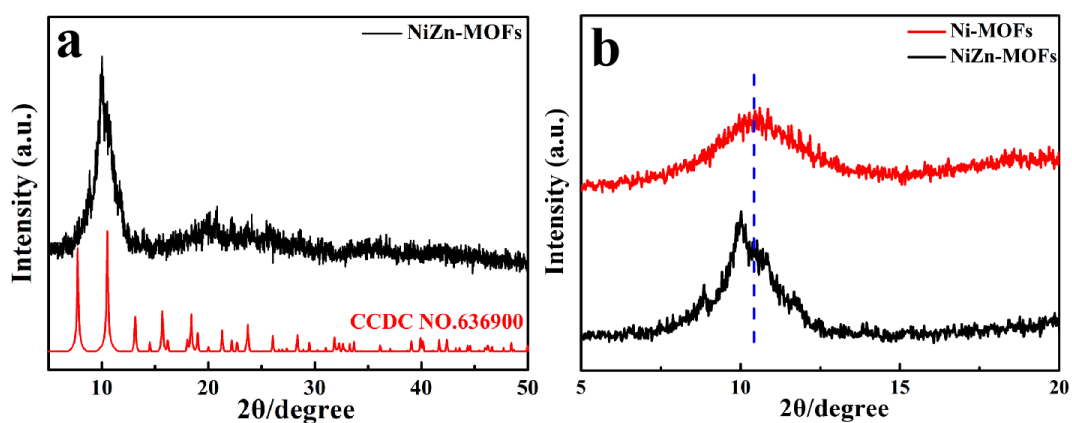


Fig. S2 (a) XRD pattern of NiZn-MOFs, (b) XRD patterns of NiZn-MOFs and Ni-MOFs from 5° to 20° .

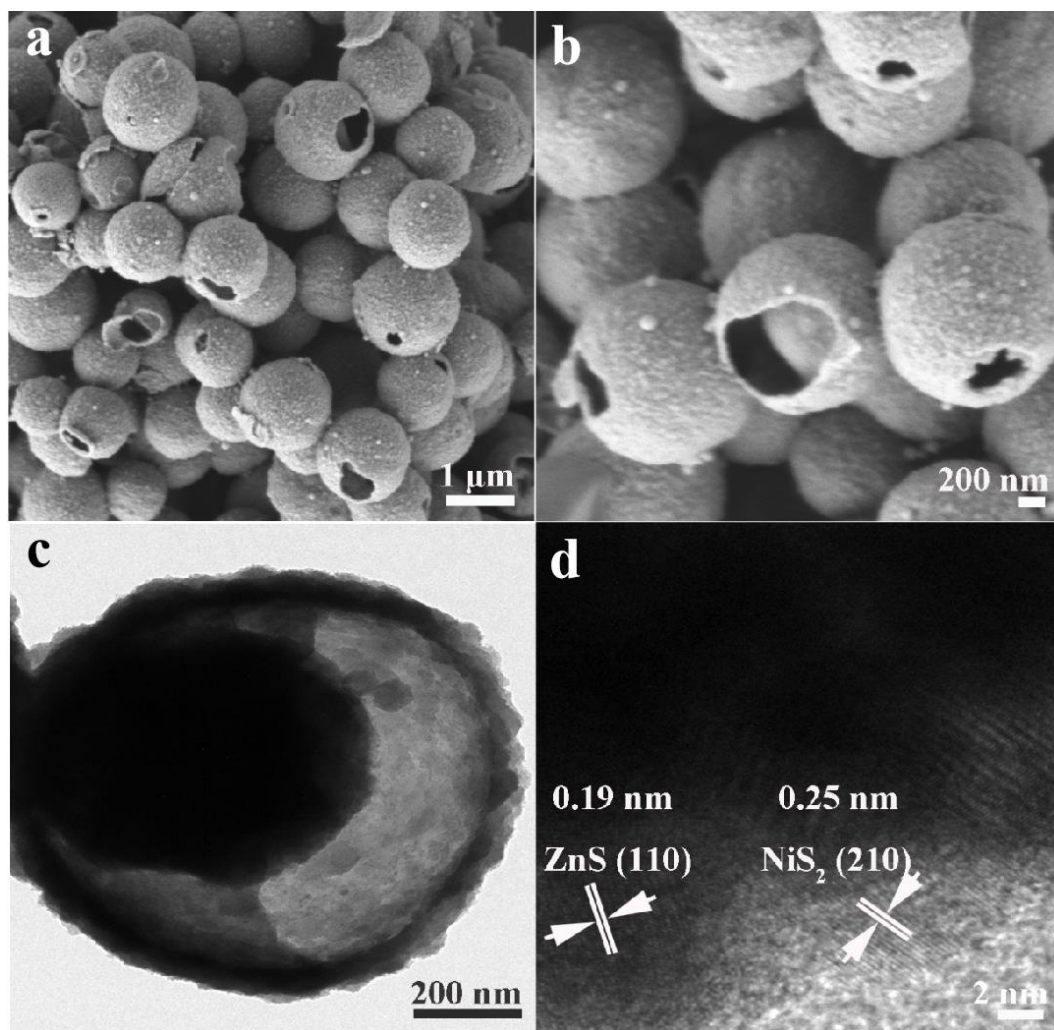


Fig. S3 FESEM (a, b), TEM (c), and HRTEM (d) images of yolk-shell NiS_2/ZnS hollow microspheres.

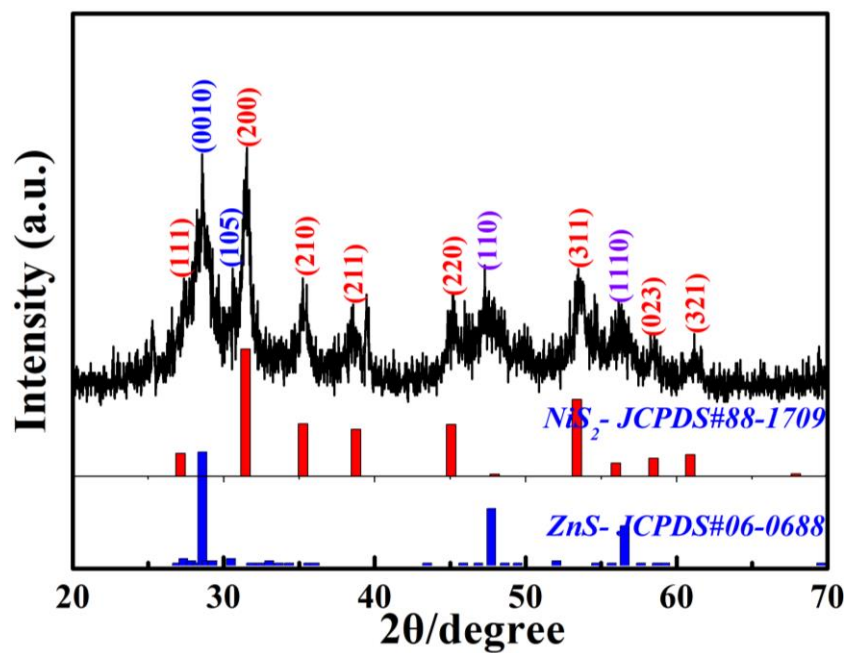


Fig. S4 XRD pattern of yolk-shell NiS₂/ZnS hollow microspheres.

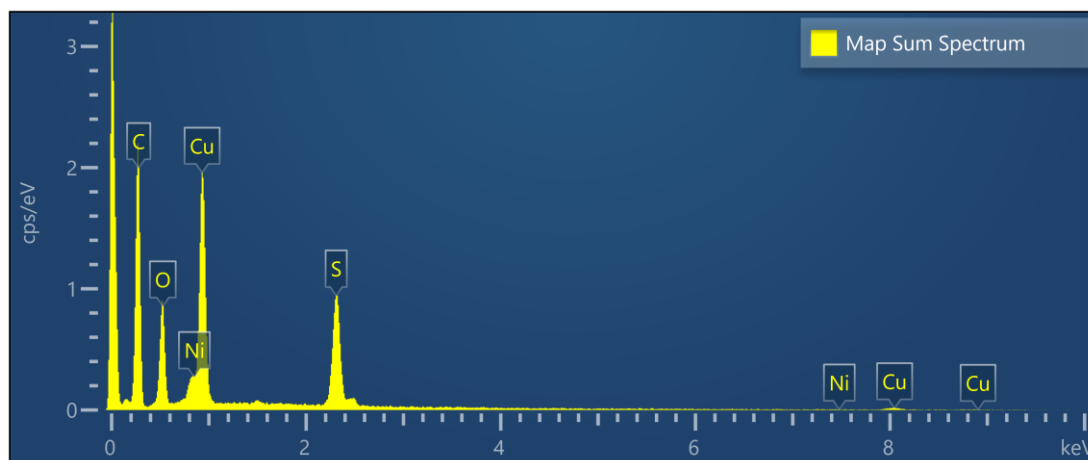


Fig. S5 EDX spectrum of yolk-shell NiS₂/CuS hollow microspheres.

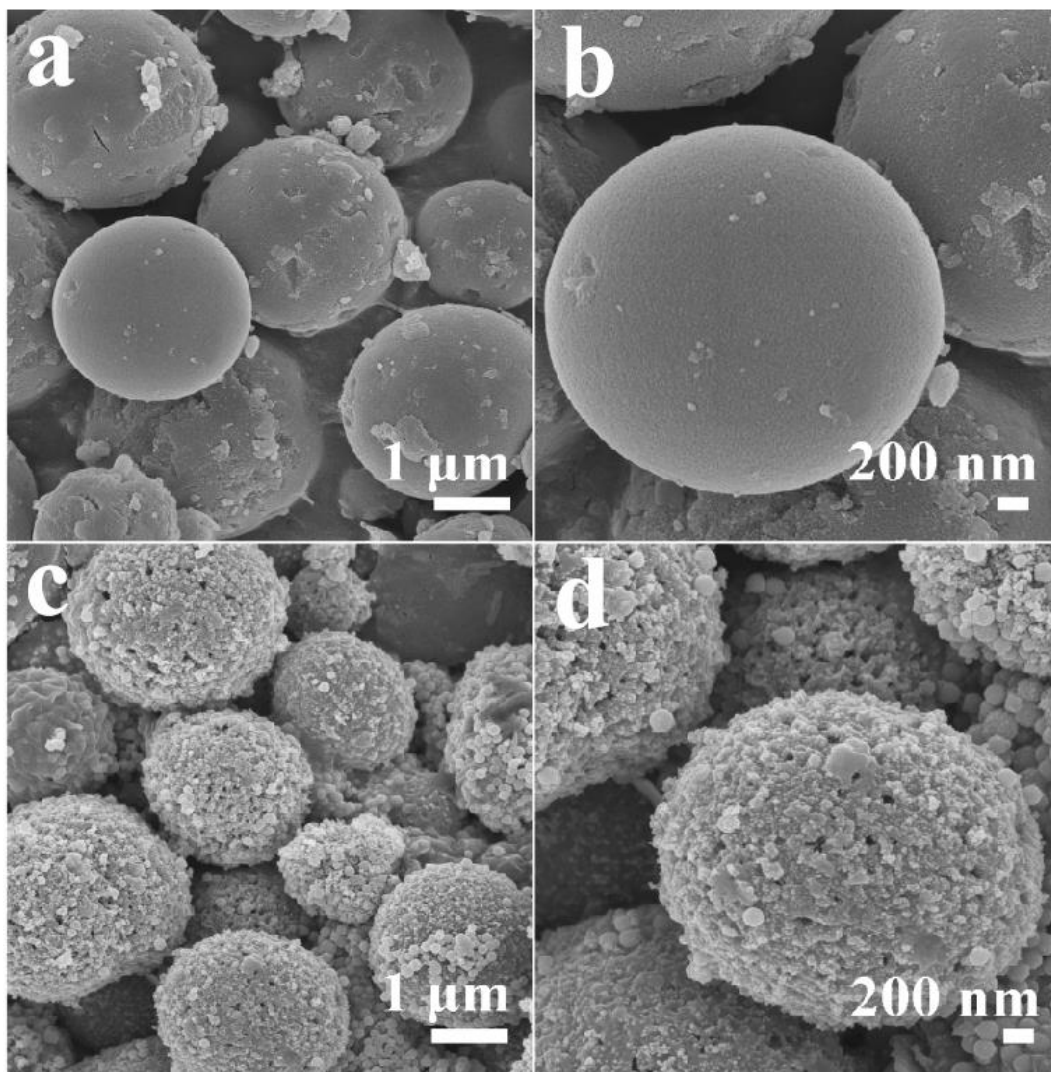


Fig. S6 SEM images of Ni-MOFs (a, b) and plain NiS₂ microspheres (c, d).

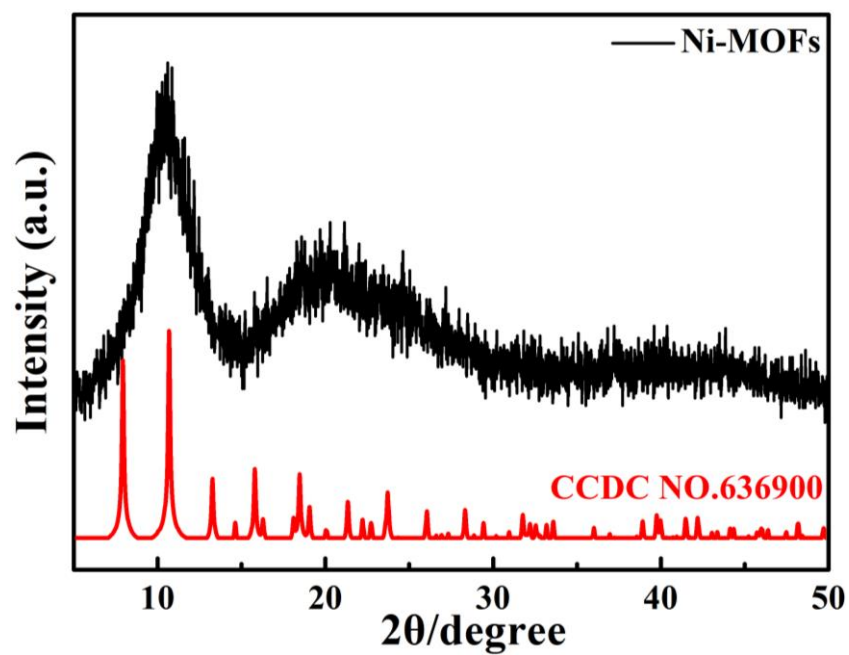


Fig. S7 XRD pattern of Ni-MOFs.

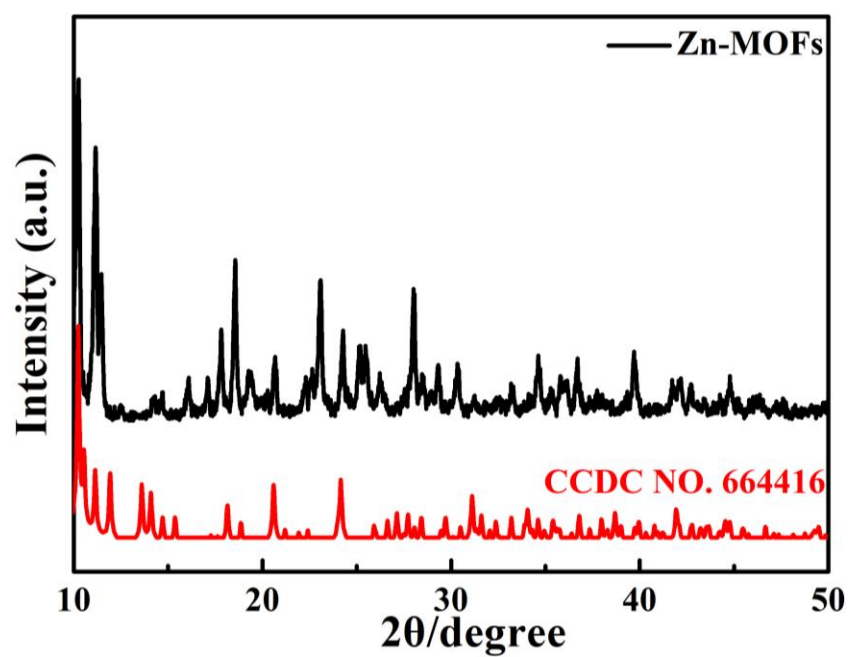


Fig. S8 XRD pattern of Zn-MOFs.

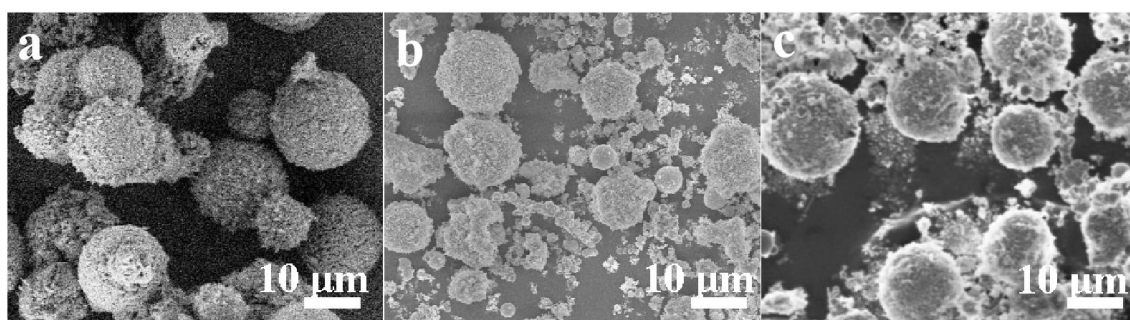


Fig. S9 SEM images of Zn-MOFs (a), ZnS (b), and CuS (c).

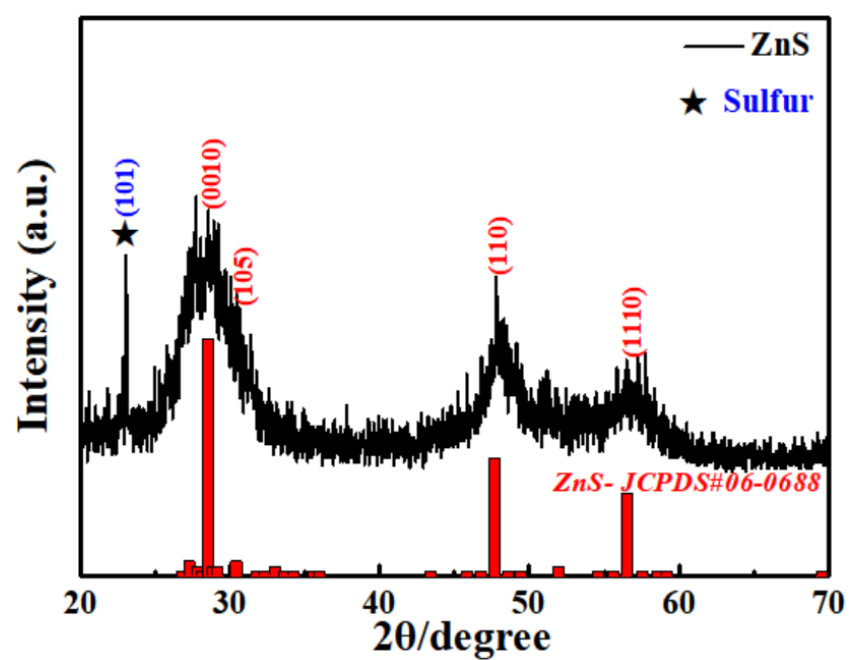


Fig. S10 XRD pattern of plain ZnS.

Table S1 ICP analysis of NiS₂/CuS and NiS₂/ZnS composites.

| Samples | Cu (Wt %) | Ni (Wt %) | Zn (Wt %) | Atomic molar ratio |
|-----------------------|-----------|-----------|-----------|--------------------|
| NiS ₂ /CuS | 30.6 | 14.25 | N | 1 : 2 |
| NiS ₂ /ZnS | N | 16.48 | 35.98 | 0.49 : 1 |

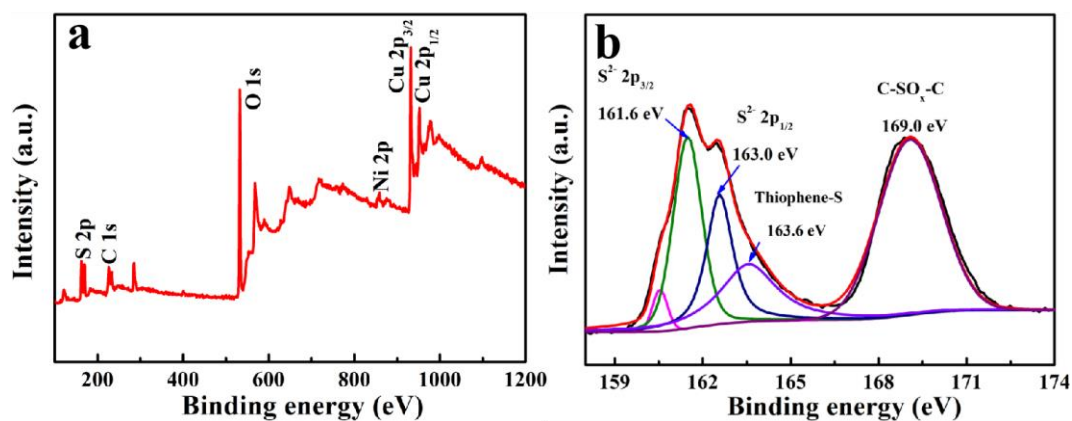


Fig. S11 XPS survey spectrum (a) and high-resolution S 2p spectrum (b) of yolk-shell NiS₂/CuS hollow microspheres.

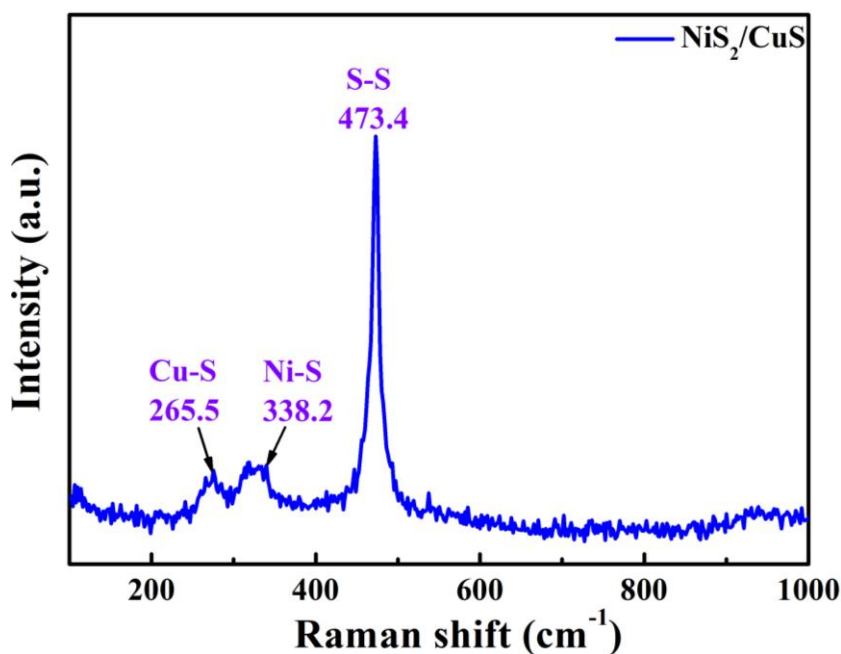


Fig. S12 Raman spectrum of yolk-shell NiS₂/CuS hollow microspheres.

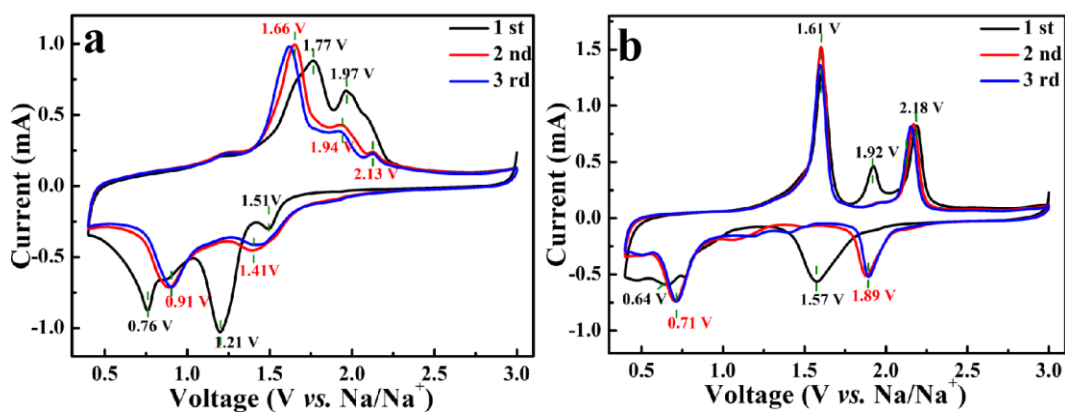


Fig. S13 The initial three CV curves of plain NiS₂ (a) and CuS (b) electrodes at a rate of 0.5 mV s⁻¹ in a potential range of 0.4 ~ 3.0 V.

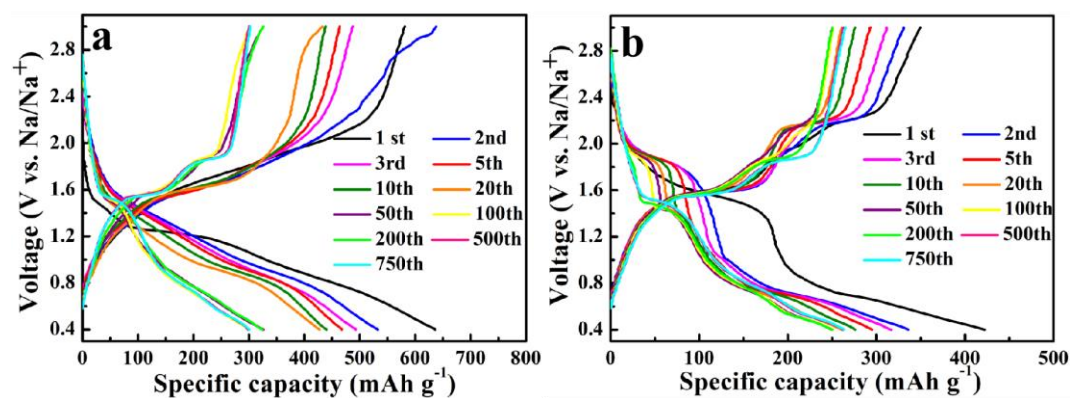


Fig. S14 The GCD profiles of plain NiS₂ (a) and CuS (b) electrodes at 2 A g⁻¹ from 1st to 750th cycle in a potential range of 0.4 ~ 3.0 V.

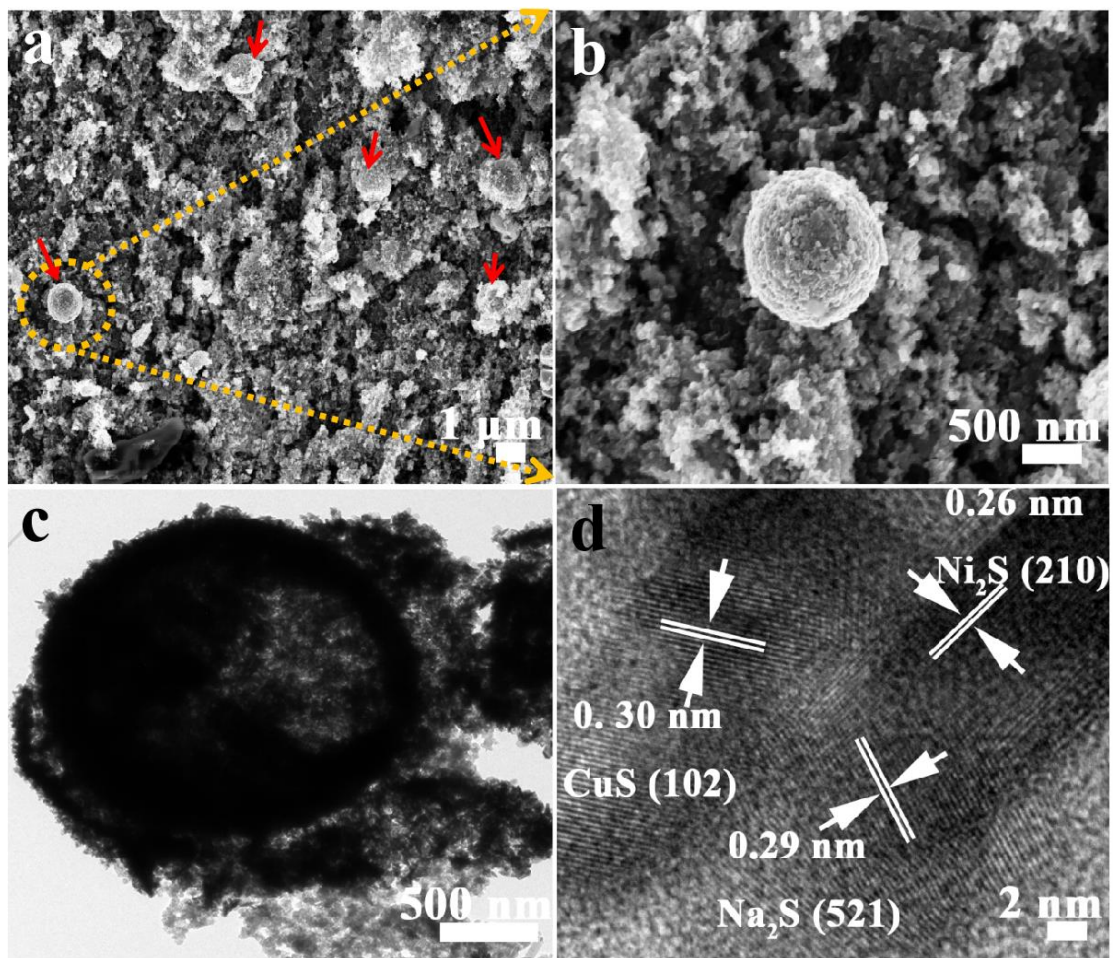


Fig. S15 The SEM (a, b), TEM (c), and HRTEM (d) images of yolk-shell NiS_2/CuS hollow microspheres after long cycles at 2.0 A g^{-1} .

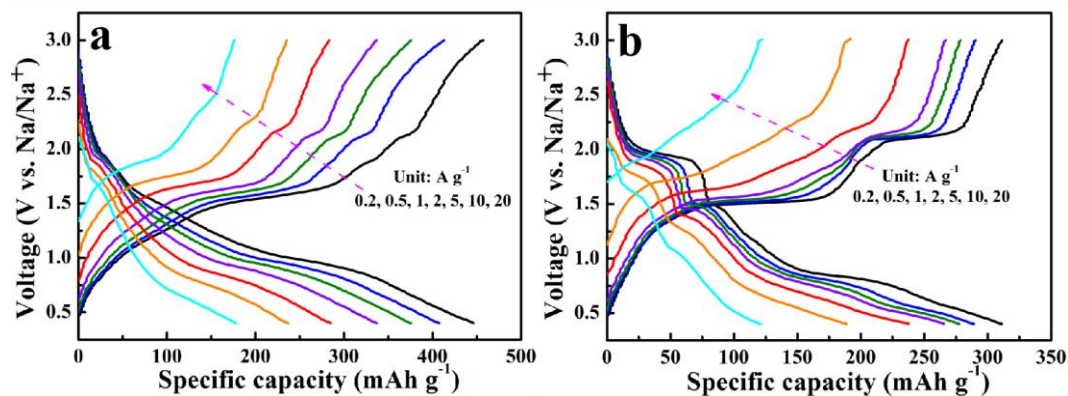


Fig. S16 The GCD profiles of plain NiS₂ (a) and CuS (b) electrodes at different current rates in a potential range of 0.4 ~ 3.0 V.

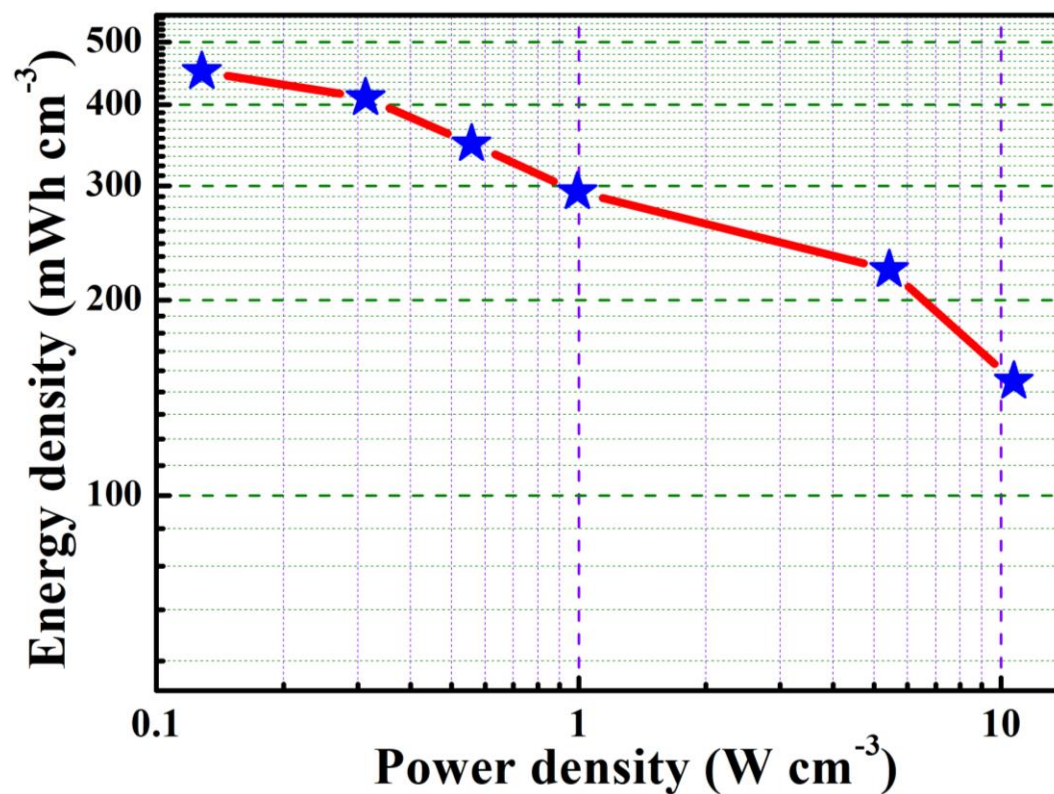


Fig. S17 Volumetric energy densities of yolk-shell NiS₂/CuS hollow microspheres at different power densities.

Table S2 A comparison of cycling performance and reversible specific capacity about NiS₂- and CuS-based anodes for SIBs.

| Materials | Voltage window (V) | Rate (A g ⁻¹) | Cycle number | Capacity (mAh g ⁻¹) | Ref. |
|---|--------------------|---------------------------|--------------|---------------------------------|------------------|
| NiS ₂ @CoS ₂ | 0.01-3.0 | 1.0 | 250 | 600.0 | 1 |
| NiS ₂ Nanospheres | 0.4-2.9 | 0.5 | 1000 | 319.0 | 2 |
| NiS ₂ nanoparticles | 0.01-3.0 | 2.0 | 1000 | 140.0 | 3 |
| pomegranate-like NiS ₂ nanoparticles | 0.01-3.0 | 0.5 | 300 | 356.2 | 4 |
| hollow NiS ₂ spheres | 0.01-3.0 | 1.0 | 300 | 530.0 | 5 |
| SnS ₂ /NiS ₂ | 0.01-3.0 | 2.0 | 100 | 343.2 | 6 |
| NiS ₂ @C | 0.01-3.0 | 0.1 | 100 | 580.8 | 7 |
| CuS Microspheres | 0.01-3.0 | 10 | 1000 | 312.5 | 8 |
| CuS Microspheres | 0.6-3.0 | 0.5 | 500 | 403.0 | 9 |
| CuS@CoS ₂ Double-Shelled Nanoboxes | 0.4-2.6 | 0.5 | 500 | 403.0 | 10 |
| N-Doped CuS@C Nanowires | 0.4-3.0 | 2.0 | 10000 | 216.7 | 11 |
| Platelet-like CuS | 0.4-2.6 | 2.0 | 500 | 320 | 12 |
| ZnS/CuS@C | 0.4-3.0 | 10.0 | 1750 | 282.7 | 13 |
| Hydrangea-Like CuS | 0.4-2.6 | 1.0 | 400 | 335 | 14 |
| NiS₂/CuS | 0.4-3.0 | 10.0 | 2150 | 371.6 | This work |
| | | 20.0 | 4200 | 283.4 | |

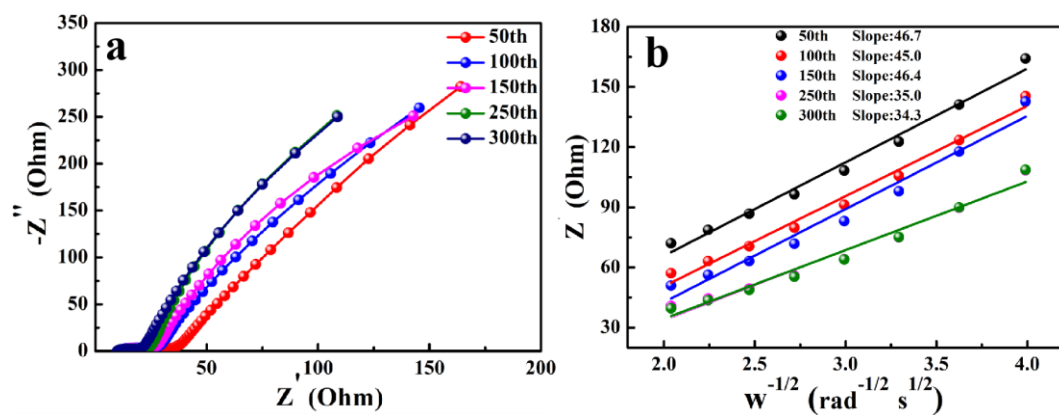


Fig. S18 Nyquist plots (a) and the linear fitting of Z' and $\omega^{-1/2}$ (b) of NiS_2/CuS electrode at different cycles.

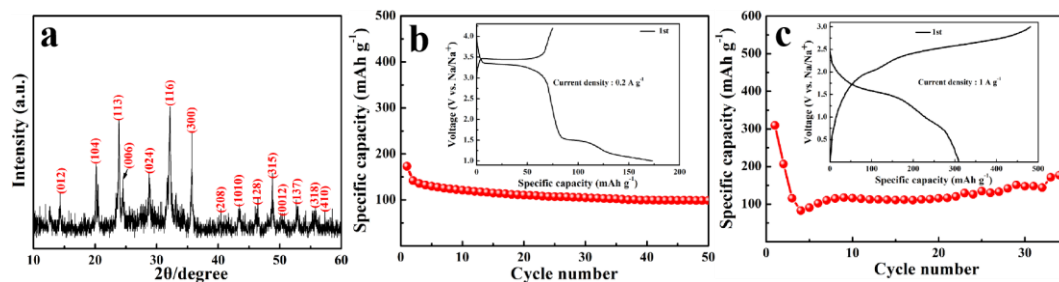


Fig. S19 (a) The XRD pattern of $\text{Na}_3\text{V}_2(\text{PO}_4)_3/\text{C}$. (b) The GCD profiles and cycling performance of $\text{Na}_3\text{V}_2(\text{PO}_4)_3/\text{C}$ electrode in a potential range of 1.0 to 4.2 V at 0.2 A g^{-1} . (c) The GCD profiles and cycling performance of $\text{Na}_3\text{V}_2(\text{PO}_4)_3/\text{C}/\text{NiS}_2/\text{CuS}$ full cell in a potential range of 0.01 to 3.0 V at 1.0 A g^{-1} .

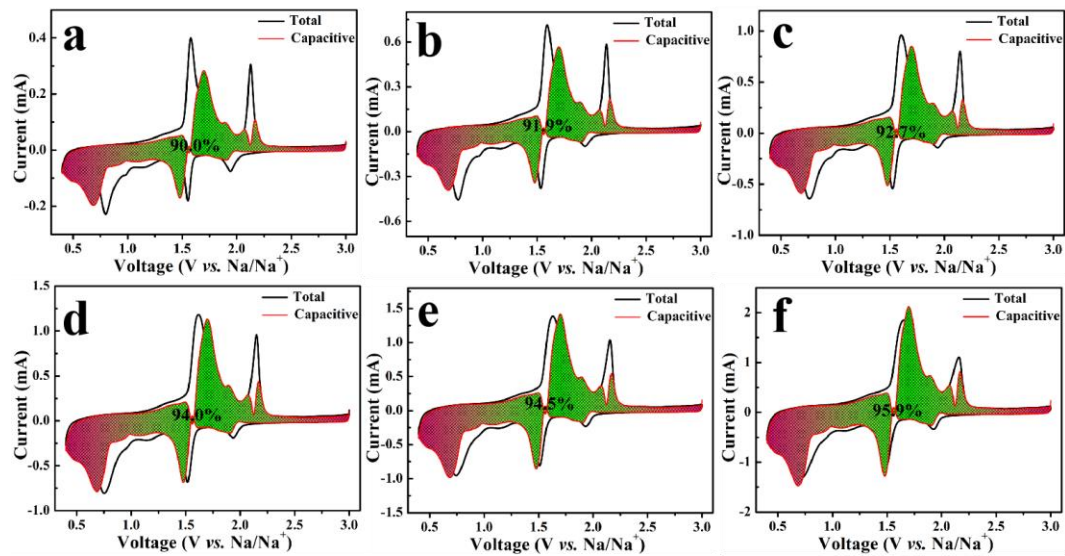


Fig. S20 The overall capacity versus pseudocapacitive fraction shown by the shaded area for NiS₂/CuS electrode at various scan rates: (a) 0.2 mV s⁻¹; (a) 0.4 mV s⁻¹; (b) 0.6 mV s⁻¹; (c) 0.8 mV s⁻¹; (d) 1.0 mV s⁻¹; (e) 1.5 mV s⁻¹.

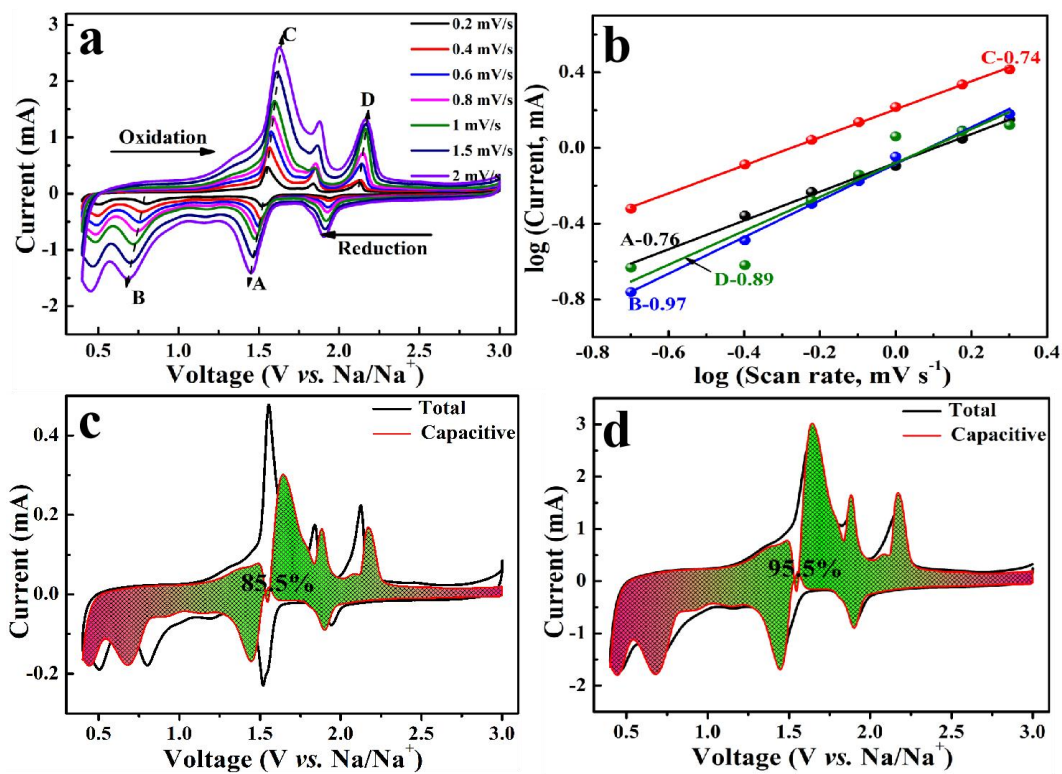


Fig. S21 (a) CV curves of plain NiS₂ electrode subjected to different scan rates from 0.2 to 2.0 mV s⁻¹. (b) The corresponding log (*i*) versus log (*v*) plots at each redox peak current. The overall capacity versus pseudocapacitive fraction shown by the shaded area at 0.2 (c) and 2.0 (d) mV s⁻¹.

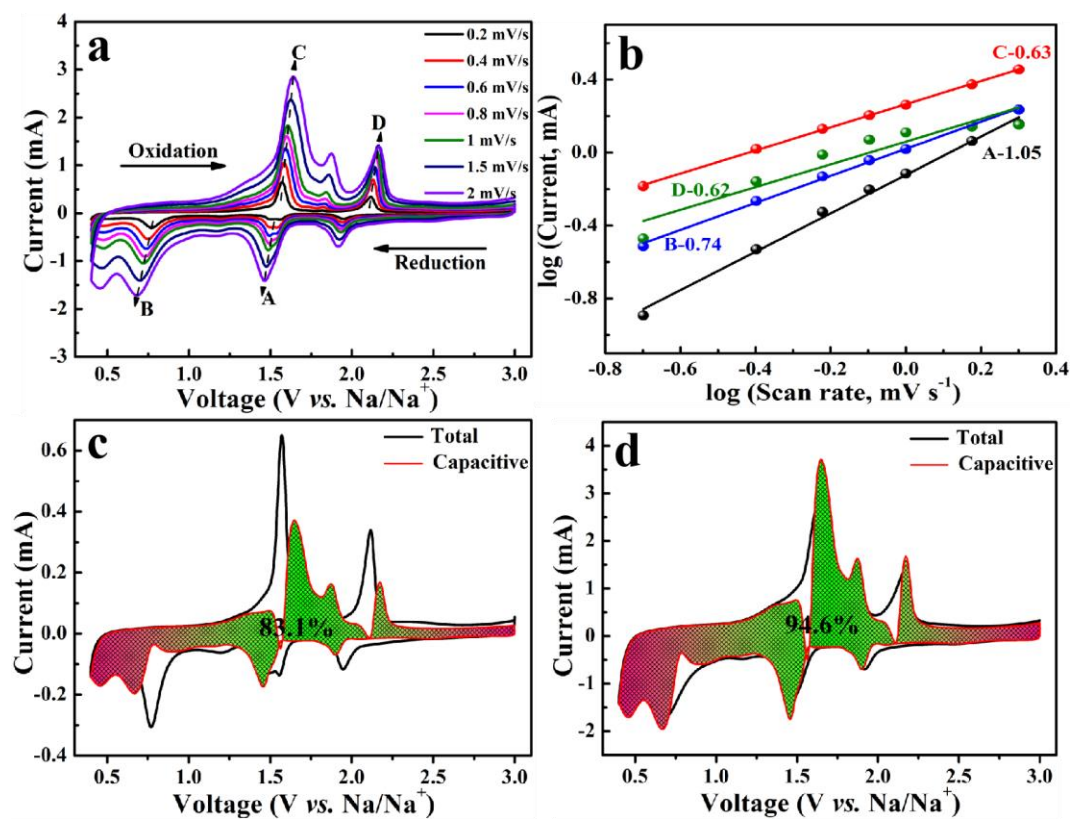


Fig. S22 (a) CV curves of plain CuS electrode subjected to different scan rates from 0.2 to 2.0 mV s^{-1} . (b) The corresponding $\log(i)$ versus $\log(v)$ plots at each redox peak current. (c) Overall capacity versus pseudocapacitive fraction shown by the shaded area at 2.0 mV s^{-1} .

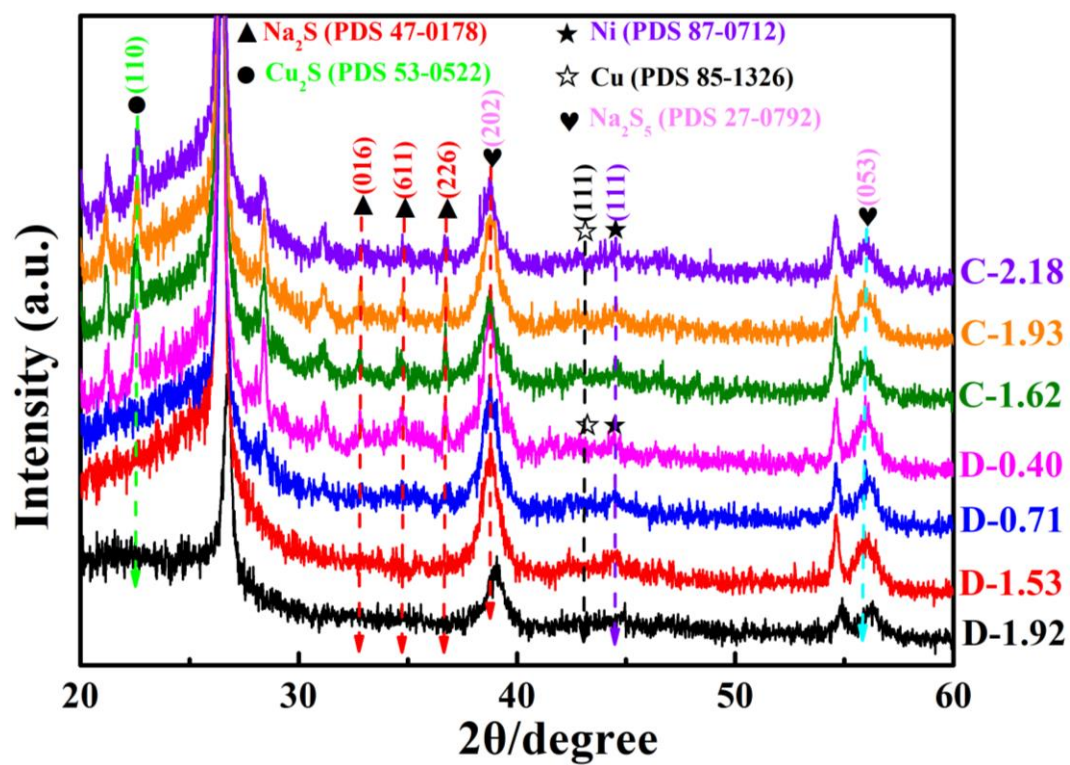


Fig. S23 The ex-situ XRD patterns of NiS_2/CuS electrode at different discharged and charged states in the second cycle.

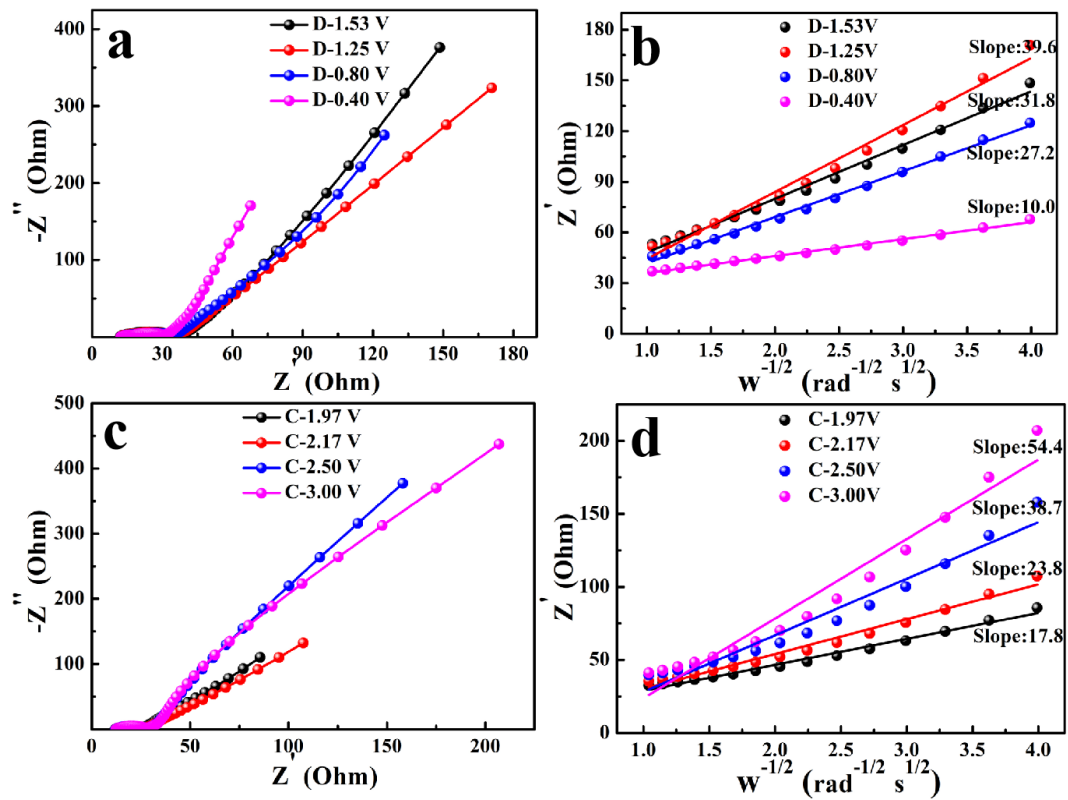


Fig. S24 Nyquist plots of NiS₂/CuS electrode at different discharged (a) and charged (c) states. The linear fitting of Z' and $\omega^{-1/2}$ of NiS₂/CuS electrode at different discharged (b) and charged (d) states.

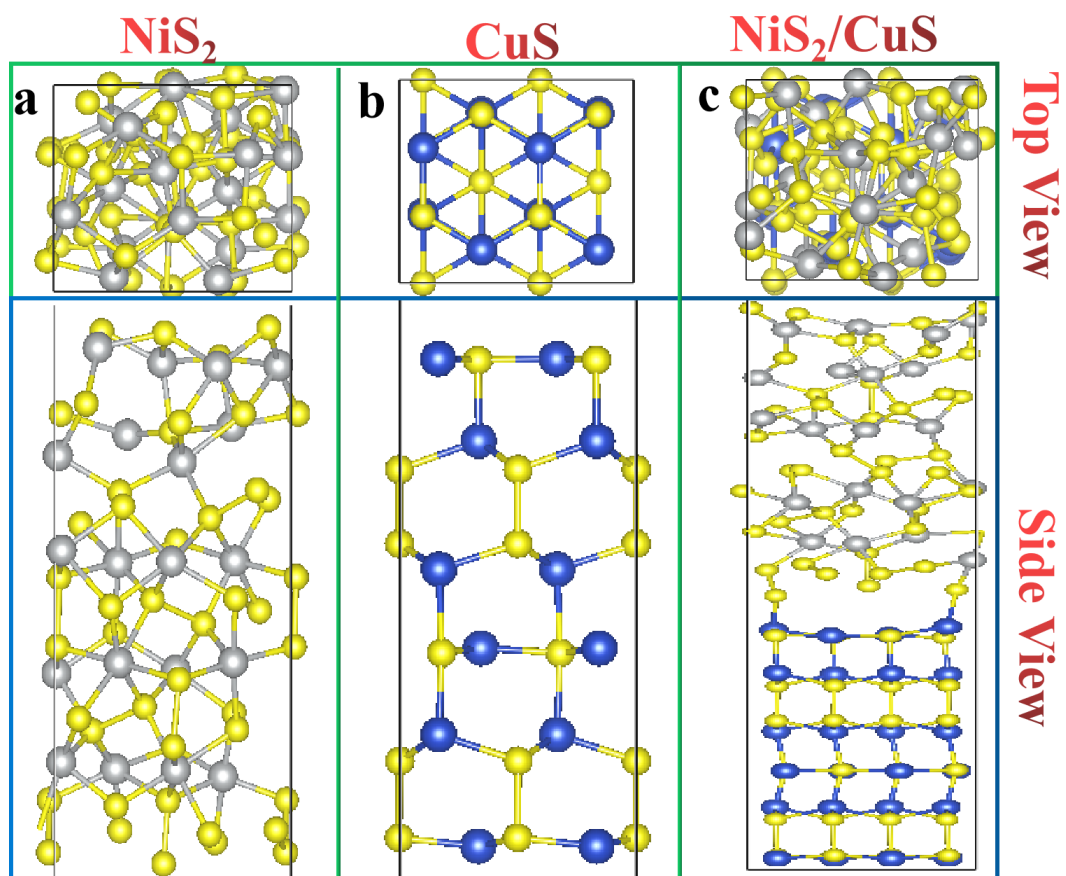


Fig. S25 Crystal structures of NiS_2 (a), CuS (b) and NiS_2/CuS (c) from top view and side view.

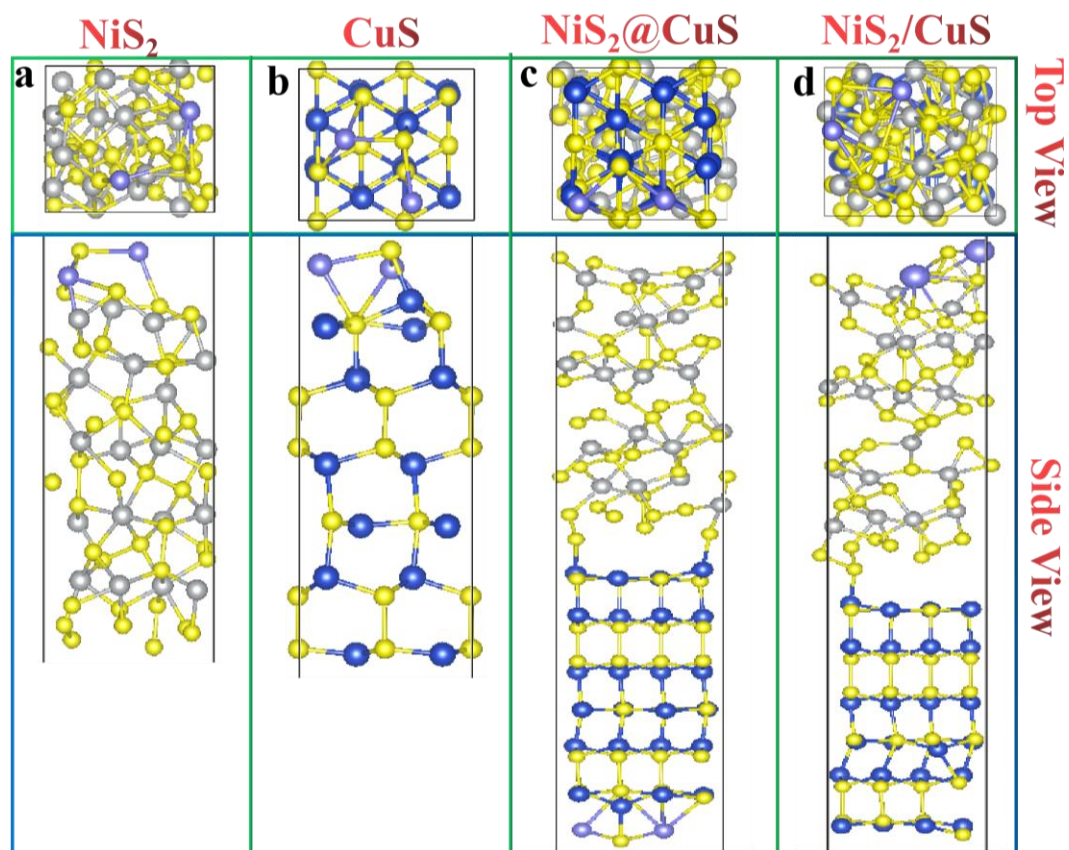


Fig. S26 The binding energies of Na_2S under the stable adsorption configuration for NiS_2 (a), CuS (b) from top view and side view. Na_2S adsorbed at CuS (c) or NiS_2 (d) crystal of NiS_2/CuS heterojunction from top view and side view.

References

- 1 Y. M. Lin, Z. Z. Qiu, D. Z. Li, S. Ullah, Y. Hai, H. L. Xin, W. D. Liao, B. Yang, H. S. Fan, J. Xu and C. Z. Zhu, *Energy Storage Mater.*, 2018, **11**, 67–74.
- 2 R. M. Sun, S. J. Liu, Q. L. Wei, J. Z. Sheng, S. H. Zhu, Q. Y. An and L. Q. Mai, *Small*, 2017, **13**, 1701744.
- 3 W. X. Zhao, S. Q. Ci, X. Hu, J. X. Chen and Z. H. Wen, *Nanoscale*, 2019, **11**, 4688–4695.
- 4 J. B. Li, J. L. Li, D. Yan, S. J. Hou, X. T. Xu, T. Lu, Y. F. Yao, W. J. Mai and L. K. Pan, *J. Mater. Chem. A*, 2018, **6**, 6595–6605.
- 5 R. Bi, C. Zeng, H. W. Huang, X. P. Wang and L. Zhang, *J. Mater. Chem. A*, 2018, **6**, 14077–14082.
- 6 S. D. Guan, T. S. Wang, X. L. Fu, L. Z. Fan and Z. J. Peng, *Appl. Surf. Sci.*, 2020, **508**, 145241.
- 7 G. G. Zhao, Y. Zhang, L. Yang, Y. L. Jiang, Y. Zhang, W. W. Hong, Y. Tian, H. B. Zhao, J. G. Hu, L. Zhou, H. S. Hou, X. B. Ji and L. Q. Mai, *Adv. Funct. Mater.*, 2018, **28**, 1803690.
- 8 Y. H. Xiao, D. C. Su, X. Z. Wang, S. D. Wu, L. M. Zhou, Y. Shi, S. M. Fang, H. M. Cheng and F. Li, *Adv. Energy Mater.*, 2018, **8**, 1800930.
- 9 H. Li, Y. H. Wang, J. L. Jiang, Y. Y. Zhang, Y. Y. Peng and J. B. Zhao, *Electrochim. Acta*, 2017, **247**, 851–859.
- 10 Y. J. Fang, B. Y. Guan, D. Y. Luan and X. W. Lou, *Angew. Chem., Int. Ed.*, 2019, **131**, 7821–7825.
- 11 D. Zhao, M. M. Yin, C. H. Feng, K. Zhan, Q. Z. Jiao, H. S. Li and Y. Zhao, *ACS Sustainable Chem. Eng.*, 2020, **8**, 11317–11327.
- 12 Z. G. Yang, Z. G. Wu, J. Liu, Y. X. Liu, S. Y. Gao, J. A. Wang, Y. Xiao, Y. J. Zhong, B. H. Zhong and X. D. Guo, *J. Mater. Chem. A*, 2020, **8**, 8049–8057.
- 13 W. X. Zhao, L. X. Gao, L. C. Yue, X. Y. Wang, Q. Liu, Y. L. Luo, T. S. Li, X. F. Shi, A. M. Asiri and X. P. Sun, *J. Mater. Chem. A*, 2021, **9**, 6402–6412.
- 14 Z. G. Yang, Z. G. Wu, W. B. Hua, Y. Xiao, G. K. Wang, Y. X. Liu, C. J. Wu, Y. C. Li, B. H. Zhong, W. Xiang, Y. J. Zhong and X. D. Guo, *Adv. Sci.*, 2020, **7**, 1903279.